DC reactive magnetron sputtering, annealing, and characterization of CuAlO$_2$ thin films

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(Received 31 August 2010; accepted 14 November 2010; published 4 January 2011)

CuAlO$_2$ thin films were prepared at three substrate temperatures ($T_s$=60, 300, and 600 °C) and two oxygen partial pressures ($P_{O_2}$=0.5 and 2 mTorr) via dc reactive magnetron sputtering from Cu–Al 50–50 at. % alloy targets and subsequent annealing. As-deposited films with $P_{O_2}$=0.5 mTorr were oxygen deficient; although the delafossite structure formed upon annealing, electrical properties were poor. Films deposited with $P_{O_2}$=2 mTorr transformed into the delafossite structure and exhibited p-type conductivity after annealing under N$_2$ at temperatures $T_A \geq 750$ °C. Conductivity generally increased with increasing $T_s$ and decreasing $T_A$. A special case of $P_{O_2}$=2 mTorr and low $T_s$ (60 °C) resulted in a partially crystalline oxide phase that transformed into the delafossite structure at $T_A$=700 °C and yielded the highest conductivity of 1.8 S cm$^{-1}$. In general, a $T_A$ near the phase formation boundary led to an increase in conductivity. Low-temperature hydrothermal annealing was also investigated and shown to produce mixed phase films exhibiting the delafossite structure along with CuO, AlOOH, and Al$_2$O$_3$. © 2011 American Vacuum Society.

[DOI: 10.1116/1.3525640]

I. INTRODUCTION

Transparent conducting oxides (TCOs) have many technological uses, including flat panel displays, photovoltaics, and low emissivity window glass.$^1$ Almost all TCOs are n-type semiconductors, but there has been considerable interest in p-type TCOs, which would have applications in transparent electronics, functional windows, and transparent complementary field-effect transistors.$^2$ Of the few transparent oxide materials exhibiting p-type conductivity, a number are from a class of delafossite structure oxides epitomized by CuAlO$_2$.$^3$ This ABO$_2$ crystal structure consists of alternating layers of B$^{3+}$O$_6$ octahedra and closest packed, linearly coordinated A$^{1+}$ cations.$^4$

Since the initial report of laser ablated CuAlO$_2$ thin films exhibiting p-type conductivity,$^3$ p-type delafossite structure CuAlO$_2$ has been synthesized by various methods including rf sputtering$^5$–$^7$ and dc sputtering.$^8$–$^{10}$ Sputter deposition is of particular interest because it is widely used in industry for depositing TCOs.$^{11}$ Two strategies have been employed to yield the delafossite phase in sputtered films, namely, direct deposition and deposition followed by annealing. Direct delafossite formation has been reported in a few cases, using both oxide and metallic targets, but conductivities were relatively low, 0.08–0.51 S cm$^{-1}$$^8$–$^{12}$ In other cases a post-deposition annealing in an inert atmosphere (Ar or N$_2$) was required to transform the films into the delafossite structure. In a case where films with varying Cu:Al ratios were obtained by reactively sputtering from separate Cu and Al targets, annealing at temperature $T_A > 700$ °C was necessary to form the delafossite structure, and a maximum conductivity of $\sim$0.1 S cm$^{-1}$ was observed.$^{10,13}$ For films sputtered from a single Cu–Al alloy target, the delafossite structure was obtained at $T_A > 600$ °C and conductivity (0.038 S cm$^{-1}$) was observed only for annealing at $T_A > 800$ °C.$^{14}$ This article describes films reactively sputtered from a single Cu–Al alloy target at various temperatures and the effects of postdeposition annealing conditions on their phase formation, crystal structure, morphology, electrical properties, and optical properties. The main aim of the work was to provide a clearer picture of the phase evolution and electrical properties upon annealing at different $T_A$, and the role of deposition conditions including oxygen partial pressure and temperature. Through studying this process, the path to the highest reported conductivity of CuAlO$_2$ films via physical
vapor deposition was discovered, $\sigma = 1.83$ S/cm. Also, initial results on hydrothermal annealing, with the potential to form the delafossite structure at lower temperature than possible using conventional annealing, are presented.

**II. EXPERIMENTAL DETAILS**

Cu–Al–O films were deposited via dc reactive magnetron sputtering in a load-locked vacuum system, described elsewhere.\(^\text{15}\) A metallic 50–50 at. % Cu–Al target of 99.99% purity was used for all of the depositions. The target to substrate distance was ~14 cm. The target was kept at a constant power of 100 W throughout the depositions.

The chamber was evacuated to a pressure of $P_{\text{tot}} < 3.0 \times 10^{-7}$ Torr, after which a mixture of argon and oxygen was leaked into the system via mass flow controllers to attain a total pressure of $P_{\text{tot}} = 5.0$ mTorr. The oxygen partial pressure was either $P_{\text{O}_2} = 0.5$ mTorr (10% oxygen) or 2.0 mTorr (40% oxygen). The substrates used in this study were single crystal c-plane sapphire. Prior to loading into the deposition chamber, the wafers were ultrasonically cleaned in acetone and methanol for 10 min each. The substrates were further cleaned in the chamber by heating to 600 °C for at least 30 min. The substrate temperature, $T_s$, during deposition, ~60 °C (no intentional heating), 300 °C, or 600 °C, was controlled via a resistively heated silicon wafer.

The composition of several as-deposited films was determined by inductively coupled plasma atomic emission (ICP-AES, Varian Vista-MPX). The films were placed in 5 ml of 5% aqua regia (by volume) in a Parr pressure vessel lined with a 23 ml Teflon polytetrafluoroethylene (PTFE) cup. After 12 h of digestion at 150 °C, no visible trace of film was left on the substrate. The Cu:Al ratio of the final solution was measured. A blank sapphire substrate was also digested by the same procedure to correct for Al that dissolved from the substrate.

Two different atmospheric annealing procedures were used in this study. The samples deposited with $P_{\text{O}_2} = 0.5$ mTorr underwent a two-step annealing, the first at moderate temperature (500–700 °C) in air with a subsequent annealing at elevated temperature (650–900 °C) under $N_2$. Samples deposited with $P_{\text{O}_2} = 2$ mTorr only required the second annealing step. For these films, a series of annealing was completed from 650 to 900 °C in 50 °C increments under $N_2$. In all annealing, the temperature was ramped to the annealing temperature at a rate of 57/min, maintained at the hold temperature for 6 h, and then cooled. Prior to the annealing process, the furnace tube was purged with nitrogen for a minimum of 12 h.

Investigations of the effects of hydrothermal annealing were also completed on the films. Hydrothermal annealing has previously been used successfully to produce highly crystalline films of $Zn_2SiO_4$, $ZrO_2$, and MnO$_2$ from films that had been deposited in an amorphous state by successive ionic layer adsorption and reaction.\(^\text{16}\) The films were placed in a Parr pressure vessel lined with 23 ml Teflon PTFE cups with 0.05–0.30 ml water. The pressure vessel was heated to a maximum of 250 °C, at which point elevated vapor pressures of 5–15 atm were obtained. Similar temperature and pressure conditions have previously been used to hydrothermally synthesize bulk CuAlO$_2$ powders.\(^\text{4}\) Several films were hydrothermally annealed at 300 °C. These films and 2.0 ml water were heated in a 300 ml stainless steel Parr pressure vessel fitted with a PTFE-flat gasket. Both 0.5 and 2.0 mTorr $P_{\text{O}_2}$ films were investigated. Annealing times varied from 6 to 24 h. To prevent excessive oxidation of the film from atmospheric $O_2$, the water was preboiled and the films were loaded and sealed in the pressure vessels under $N_2$.

Films were characterized with grazing incidence x-ray diffraction (XRD) using a Rigaku ATX-G diffractometer and $2\theta$–$\theta$ x-ray scans using a Rigaku RU-200PL diffractometer. Films were also examined by atomic force microscopy (AFM, Nanoscope) to determine surface roughness. Film thickness was measured with a Tencor P10 surface profilometer.

Annealed films that showed a predominantly delafossite phase by XRD underwent electrical measurements (BioRad HL5500 and hot-probe device) and optical measurements for band gap and transparency (Cary 500 scan UV-VIS-NIR). Selected samples were also examined with scanning electron microscopy (SEM, Hitachi S-4800-II microscope).

Due to the high resistivity and high carrier concentration of the samples, Hall measurements in standard $B = 0.3$ T tabletop magnets may not be reliable. Thus for Hall measurements, a superconducting 15 T magnet was used with a helium flow cryostat operating at 300 K. Van der Pauw measurements of high resistivity samples inevitably mix a component of the longitudinal resistance $R_{xx}$ with the Hall signal $R_{xy}$. Since thermal fluctuations of order of 0.5 K cannot be avoided, the large thermal coefficient of $R_{xx}$ results in drifting signals that can overwhelm the small Hall signal. To eliminate this effect, a scaled component of the simultaneously measured longitudinal resistance is subtracted from the Hall measurement to yield a pure $R_{xy}$ trace. Best results were obtained by difference averaging $R_{xy}(+B)$ up sweep with $R_{xy}(-B)$ down sweep. By averaging 36 Hall measurement sweeps to 15 T, the noise was reduced enough to determine a Hall coefficient.

Temperature dependent electrical measurements were completed on select films using an Oxford variable temperature insert helium flow cryostat from 300 to 80 K. Standard lock-in techniques at 2.125 Hz measured both the current and the four-point voltage under a $V_{ac} = 0.6$ V excitation. Van der Pauw four-point conductivities at 300 and 250 K were used to calibrate the two-point conductivity versus temperature curve.

**III. RESULTS AND DISCUSSION**

**A. As-deposited films**

The composition of the films was verified to be 1:1 Cu:Al by ICP-AES. This composition agrees with that of the sputtering target, indicating that the sputtering was carried out under a steady state condition. A deposition time was chosen to create 200–300 nm thick films, as verified by profilometry.
These films all had a dark brown/black coloration and were not transparent to visible light, consistent with the conclusion that they were not fully oxidized.

Increasing $P_{O_2}$ yielded increasingly oxidized films, with the films becoming visually transparent for $P_{O_2} > 1$ mTorr. Figure 1(b) shows the XRD scans from films grown with $P_{O_2} = 2$ mTorr, typical of fully oxidized films. The crystallinity of the films was dependent on $T_S$. While the $T_S \approx 60$ °C films had little observable structure, peaks were observed at higher $T_S$ that indexed to various oxide phases, including CuO and CuAl$_2$O$_4$, indicating that the films were fully oxidized. At no point was delafossite CuAlO$_2$ observed in as-deposited films. This lack of a delafossite phase agrees with prior reports for films deposited under similar conditions, where it was found that delafossite formation required $T_S \simeq 700$ °C, higher temperatures than used in the present study.

Surface roughness, as measured by AFM, increased with increasing $T_S$. Films deposited at $\approx 60$ °C had smooth surfaces with rms roughness of $\approx 0.2$ nm. Films deposited with $T_S = 300$ and $600$ °C had rms roughness values of 0.5 and 2.2 nm, respectively.

### B. Ambient-pressure annealed films

#### 1. Structure of films deposited with low $P_{O_2}$

Given that the films deposited at $P_{O_2} = 0.5$ mTorr were partially metallic, it was required that the annealing procedure should also oxidize the films. A variety of single-step oxidizing annealing procedures were attempted, but none of these yielded delafossite phase films. A two-step annealing process was thus used, namely, an annealing at temperature $T_A = 500–700$ °C in air and followed by an annealing at higher temperatures ($T_A = 700–900$ °C) under nitrogen flowing at 50 SCCM (SCCM denotes cubic centimeter per minute at STP). An example of the structural evolution can be seen in the XRD scans in Fig. 2. Under the air annealing, the partially metallic as-deposited film was fully oxidized, exhibiting CuO peaks in XRD with no metallic Cu present. The film then formed the delafossite phase during a reducing annealing at 900 °C in N$_2$.

While the two-step annealed films exhibited the desired delafossite structure, their properties were not ideal. First, the films had high surface roughness (50 nm rms). Second, the conductivities were quite low with the highest measured at 0.02 S cm$^{-1}$ and most films showing values too low to measure ($< 0.01$ S/cm). Thus, subsequent annealing studies were carried out using films deposited with $P_{O_2} = 2$ mTorr.

#### 2. Structure of films deposited with high $P_{O_2}$

Films deposited with $P_{O_2} = 2$ mTorr and either $T_S = 60, 300$, or $600$ °C were annealed in dry N$_2$ from $T_A = 650$ to 900 °C. Relatively little change in structure resulted from annealing at $T_A < 650$ °C with the XRD similar in appearance to that of the as-deposited films (Fig. 1). Figure 3(a) shows grazing incidence XRD data from $T_S \approx 60$ °C films after annealing at three different temperatures. At $T_A$...
At $T_A=650^\circ\text{C}$, the films consisted of CuO, spinel CuAl$_2$O$_4$, and possibly amorphous alumina. At $T_A=700, 750^\circ\text{C}$, and above (not shown), the delafossite peaks dominated the XRD scans. Figure 3(b) shows grazing incidence XRD scans from films deposited at $T_S=600^\circ\text{C}$. The phases observed after annealing were similar to those for films deposited at $T_S=60^\circ\text{C}$, but formation of the delafossite phase was delayed until $T_A=750^\circ\text{C}$. It is perhaps reasonable that the delafossite phase appeared only at higher $T_A$ in the films deposited at higher $T_S$ because it may have been more difficult for the delafossite phase to replace crystalline phases that were already well-established prior to annealing. A similar delay of delafossite formation was also seen in the films grown at 300 °C. Annealing temperatures at or above 750 °C were sufficient to produce the delafossite structure, as measured by XRD for all $T_S$.

Figure 4 summarizes the above results in a map of the phases present versus growth and annealing temperature in as-deposited and annealed films. Films were deposited with $P_{O_2}=2$ mTorr and annealed under N$_2$. CuO, CuAl$_2$O$_4$, and CuAlO$_2$ are represented by white, dark gray, and gray respectively.

\[
\text{CuO} + \text{Al}_2\text{O}_3 \rightarrow \text{CuAl}_2\text{O}_4, \quad (1)
\]
CuAl$_2$O$_4$ + CuO → 2CuAlO$_2$ + 1/2O$_2$. \hspace{1cm} (2)

Oxygen generation in the second reaction indicates that a reducing atmosphere should promote delafossite formation, which was observed in previous reports.$^{10,13,14}$ An equilibrium stability diagram at 1000 °C showed that the delafossite structure forms at low $P_{O_2}$=0.05 mTorr up to atmospheric conditions.$^{19,20}$

All films that fully transformed into the delafossite structure shared some common structural characteristics. The 2θ-θ x-ray scans (not shown) indicated a (001) preferred out-of-plane orientation, although weaker (101) and (012) peaks were also present. This preferred orientation agrees with prior work.$^{3,21}$ In general, a higher $T_S$ led to a stronger (001) orientation based on the peak intensity ratios between (001) and (101) or (012). The degree of orientation cannot be seen in the grazing incidence XRD data presented in Figs. 2 and 3.

Grain sizes were calculated from the 2θ-θ XRD scans using Scherrer’s formula and were found to vary between 60 and 110 nm. In general, high $T_S$ and low $T_A$ resulted in the smallest grain sizes, with the largest grains coming from 60 °C deposition and 900 °C anneal. The films did not show an epitaxial orientation relative to the sapphire substrate as tested by x-ray Φ scans.

After annealing, film surface rms roughness measured by AFM ranged from 2–4 nm, with no clear dependence on deposition conditions. This represented an increase in film surface roughness after annealing compared with the as-deposited roughness of 0.2 to 2.2 nm (see Sec. III A). The increase was most noticeable for low $T_S$ films that had low as-deposited roughness values. In films annealed at $\approx$800 °C, only a small-scale (submicrometer) lateral surface morphology was present, as seen in Fig. 5(a). These submicrometer features are believed to be the grains and match well with the calculated grain size. Films annealed at $T_A \geq 850$ °C had a second, larger-scale surface structure. Figure 5(b) shows a SEM micrograph of these features, with a lower magnification seen in Fig. 5(c). As shown in the AFM image in Fig. 5(d), large plateaus with a height of ~5–10 nm were apparent. The larger-scale morphological features were not related to any compositional nonuniformity across the film, as verified by SEM-energy dispersive x-ray spectroscopy. The contrast differences of these features, shown in Figs. 5(b) and 5(c), are instead attributed to orientation variation across the sample. This variation could be caused by slight angular differences of the surface normal, such as those observed in AFM [Fig. 5(d)], or by long-range ordering among the submicrometer grains.

The submicrometer column/void structure is similar to prior observations on Cu–Al–O films annealed at 800 and 900 °C.$^{14}$ The mosaic structure was attributed to recrystallization of the films. The smaller voids could be attributed to shrinkage during crystallization coupled with the release of O$_2$ gas when the phases transformed from the initial amorphous Al$_2$O$_3$–CuO to crystalline CuAlO$_2$. When undergoing the transformation from a mixture of CuAl$_2$O$_4$+CuO to 2CuAlO$_2$, the average unit cell molar volume decreases by 7.5%. There is also expected to be an increase in density when going from an amorphous structure to a crystalline structure.$^{22-24}$

C. Delafossite film properties

This section deals only with the annealed films deposited with $P_{O_2}=2$ mTorr described above that showed predominantly the delafossite structure.

Figure 6 shows a typical result of optical transmission measurements. The highest transparency measured at 550 nm was in films deposited at 600 °C, with the highest percent transmission of 75% after an 850 °C annealing for a film 185 nm thick. The band gaps of the films were derived by fitting the linear portion of the absorption spectra.$^{25}$ Most films had calculated band gap values between 3.5 and 3.9 eV with no clear trends with $T_A$. However, films deposited at $T_A=600$ °C had band gap values ~0.1 eV higher than films grown at lower $T_A$. These values fall mostly in the range of previously reported band gaps of 3.5–3.75 eV.$^{8,10,14}$
All films in the delafossite structure exhibited p-type conductivity based on hot-probe measurements. This was also verified by the sign of the Hall coefficient during temperature dependent analysis. Figure 7 shows the results of electrical conductivity measurements on delafossite films versus $T_S$ and $T_A$. The conductivity generally increased with decreasing $T_A$, with the $T_S=60$ °C, $T_A=700$ °C film showing by far the highest conductivity of 1.8 S/cm in a single sample with an average conductivity of 1.16 S/cm across multiple samples. This average value is comparable to the best reported conductivities for CuAlO$_2$ thin films grown by physical vapor deposition methods. The present results show that the highest conductivity was achieved at the lowest $T_A$ value that produced the delafossite phase. The dominant mechanism for p-type conduction in CuAlO$_2$ films is from the combination of $O$ interstitials ($O^+$), and Cu and Al vacancies ($V^+_Cu$ and $V^+_Al$). Oxygen vacancies, however, would have a detrimental impact on conductivity by compensating charge carriers in CuAlO$_2$ films that would decrease the conductivity. The lower annealing temperature allows for more $O^+$ and fewer oxygen vacancies, which is consistent with the decreasing conductivity for higher annealing temperatures. The combination of the low substrate temperature, $T_S=60$ °C, and high $P_{O_2}=2$ mTorr yielded a mixture of as-deposited amorphous oxides. This initial microstructure formed the delafossite structure upon annealing with the most ease compared to the other as-deposited films that also contributed to the high conductivity.

Temperature dependent conductivity is shown in Fig. 8 for a film with $T_S=60$ °C and $T_A=700$ °C and a room temperature conductivity of $\sigma=0.26$ S/cm. The Hall coefficient at room temperature was positive with a measured carrier concentration of $5 \times 10^{19}$ cm$^{-3}$. The sample conductivity decreases as temperature decreases from 300 to 80 K. In the higher temperature range ($T>190$ K), the conductivity obeys an Arrhenius activated behavior $\sigma=\exp(-E_a/k_BT)$ with activation energy $E_a=270$ meV, slightly larger than the 200 meV activation of Kawazoe et al., and in line with the measurement by Banerjee et al. of 260 meV. This value is far smaller than half of the band gap ($\sim 3.5$ eV) as pointed out by Kawazoe et al., who interpreted $E_a$ as the activation energy from dopant band to valence band. Another possible interpretation is that $E_a$ might correspond to activated hopping within the dopant band itself, in that case, the dopant binding energy could be significantly larger than $E_a$. At lower temperature below ~190 K, the conductivity transitions to a variable range hopping law $\sigma=\exp[-(T_d/T)^{1/4}]$, as seen in the inset of Fig. 8, indicating that the Fermi energy is definitely within the doping band at these temperatures as pointed out in Ref. 3. The variable range hopping temperature scale is $T_d^{1/4}=145$ K$^{1/4}$ comparable but somewhat larger than the value seen in the data of Ref. 3.

Hall measurements at room temperature show p-type conduction with a carrier density of the order $p=5 \times 10^{19}$ cm$^{-3}$ and Hall mobility of $\mu=0.03$ cm$^2$/V·s. This carrier density and mobility are comparable to Yanagi et al., but is more than two orders of magnitude larger than Kawazoe et al., suggesting that extra care may be required for reliable Hall data.

D. Hydrothermally annealed films

Films grown in both high (2 mTorr) and low (0.5 mTorr) $P_{O_2}$ were studied using the hydrothermal annealing method. Films deposited at low $P_{O_2}$, which had a large concentration of metallic copper, were not robust enough to withstand the hydrothermal environment. During the annealing process, the films detached from the substrate. Therefore, further study was done for films deposited with $P_{O_2}=2$ mTorr.

The films were observed by XRD after hydrothermal annealing at various times, temperatures, and vapor pressures. None of the films were phase-pure delafossite; they generally exhibited mixed phases of delafossite CuAlO$_2$, CuO, AlOOH (boehmite), and probably amorphous alumina. Figure 9 shows the XRD scans from films that exhibited the strongest delafossite phase peaks, for $T_A=60$ and 300 °C, and annealing at 250 °C under ~12 atm water vapor for relatively long times. The following summarizes the effects of hydrothermal annealing temperature, pressure, and time on the observed phases. Films annealed at 150 °C for 12 h under ~12 atm remained amorphous. Films deposited with $T_S=60$ and 300 °C and annealed at $T_A=250$ and 300 °C for 12
films were not obtained, with further study, hydrothermal annealing may provide a low-temperature route to phase-pure delafossite films.

ACKNOWLEDGMENTS

This material is based on the work supported by the MRSEC program of the National Science Foundation (Grant No. DMR-0520513) at the Materials Research Center of Northwestern University and made use of the J. B. Cohen X-Ray Diffraction Facility and the EPIC and NIFTI facilities of NUANCE supported by NSF-NSEC, NSF-MRSEC, Keck Foundation, the State of Illinois, and Northwestern University.